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40V +175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D T _A = +25°C	
40V	$15m\Omega$ @ $V_{GS} = 10V$	8.6A	
40 V	$20m\Omega$ @ $V_{GS} = 4.5V$	7.5A	

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$, yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

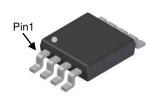
- DC-DC Converters
- Power Management Functions
- Backlighting

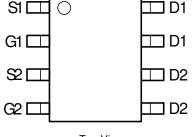
Features and Benefits

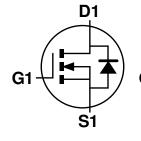
- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Data Sheet (<u>DMNH4015SSDQ</u>)

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (Approximate)







G2 S2

Top View

Top View Pin Configuration

Equivalent Circuit

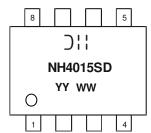
Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH4015SSD-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



>\\ = Manufacturer's Marking
NH4015SD = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 - 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	40	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note C) V 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	8.6 6.9	А
Continuous Drain Current (Note 6) V _{GS} = 10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	11.0 8.8	А
Maximum Body Diode Forward Current (Note 6)	I _S	2.2	Α		
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%	I _{DM}	80	Α		
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	25	Α		
Avalanche Energy (Note 7) L = 0.1mH	Eas	33	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P _D	1.4	w
Total Fower Dissipation (Note 3)	$T_A = +70^{\circ}C$	r _D	0.9	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	ReJA	111	°C/W
Thermal nesistance, sunction to Ambient (Note 3)	t<10s	ПӨЈА	66	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	P _D	2.0	°C/W
Total Fower Dissipation (Note o)	$T_A = +70$ °C	r D	1.2	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	75	
memai nesistance, sunction to Ambient (Note 6)	t<10s	$R_{ heta JA}$	45	
Thermal Resistance, Junction to Case (Note 6)	ReJC	13		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C	

Notes:

^{5.} Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{7.} I $_{AS}$ and E $_{AS}$ rating are based on low frequency and duty cycles to keep T_{J} = +25°C.

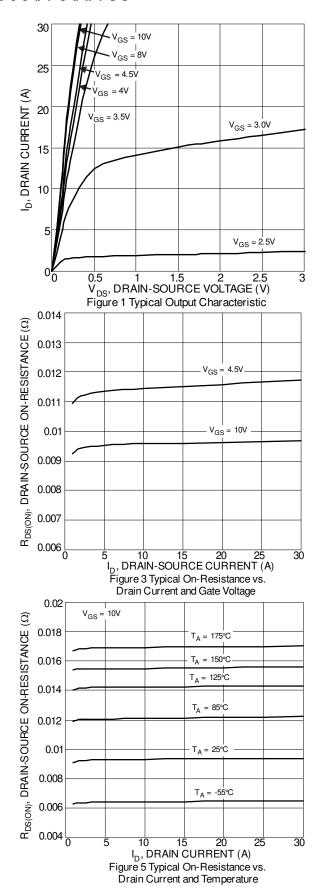


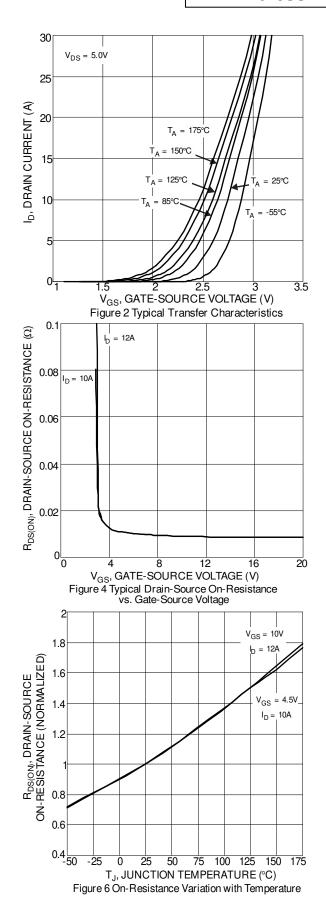
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 40V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Dec. (a.)	_	10	15	mΩ	V _{GS} = 10V, I _D = 12A	
Static Drain-Source On-nesistance	R _{DS(ON)}	_	12	20	11177	V _{GS} = 4.5V, I _D = 10A	
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	V _{GS} = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{ISS}		1,938	_		V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	156	_	pF		
Reverse Transfer Capacitance	C _{RSS}	_	126	_			
Gate Resistance	R _G	_	1.8	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_G	_	15	_			
Total Gate Charge (V _{GS} = 10V)	Q_G	_	33	_	nC	V _{DS} = 15V. I _D = 12A	
Gate-Source Charge	Q _{GS}	_	4.4	_	110	V _{DS} = 13V, I _D = 12A	
Gate-Drain Charge	Q_{GD}	_	5.9	_			
Turn-On Delay Time	t _{D(ON)}	_	4.4	_			
Turn-On Rise Time	t _R	_	10.5	_	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	12.3	_	115	$R_L=1.25\Omega,R_G=3\Omega,$	
Turn-Off Fall Time	t _F	_	5.7	_			
Body Diode Reverse Recovery Time	t _{RR}		11	_	ns	1 10A di/dt 500A/vo	
Body Diode Reverse Recovery Charge	Q _{RR}		7.6	_	nC	I _S = 12A, di/dt = 500A/μs	

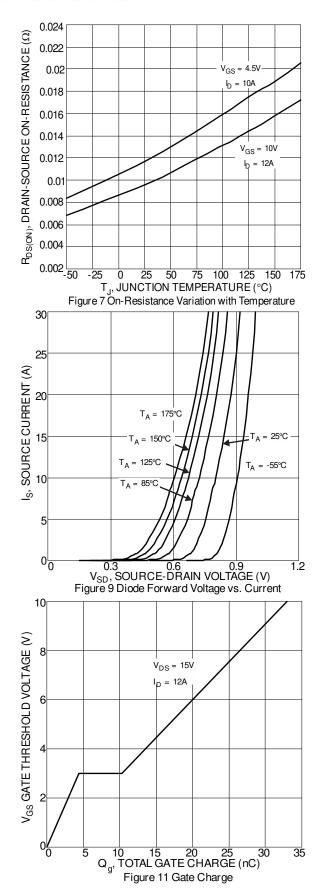
8. Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.

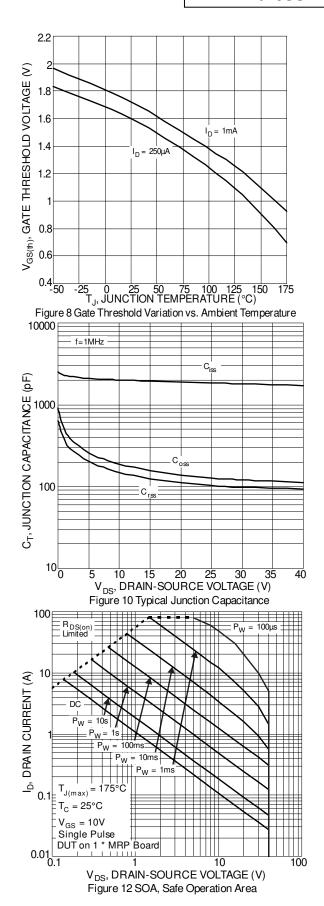




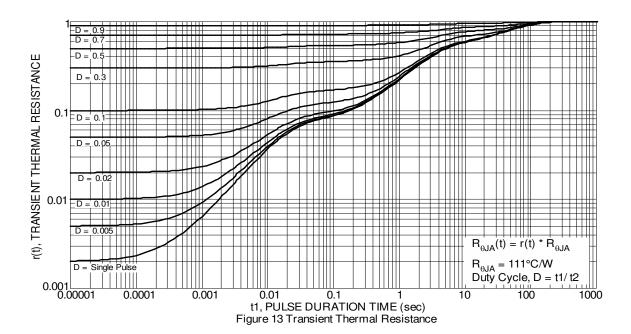










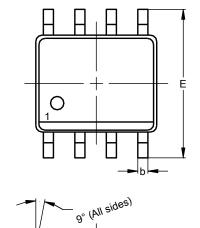


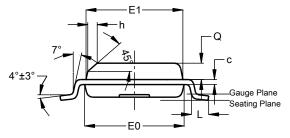


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8

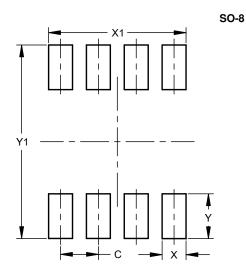




20.0						
SO-8						
Dim	Min	Max	Тур			
Α	1.40	1.50	1.45			
A1	0.10	0.20	0.15			
b	0.30	0.50	0.40			
С	0.15	0.25	0.20			
D	4.85	4.95	4.90			
Е	5.90	6.10	6.00			
E1	3.80	3.90	3.85			
E0	3.85	3.95	3.90			
e 1.27						
h 0.3						
L	0.62	0.82	0.72			
Q	0.60	0.70	0.65			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Υ	1.505
Y1	6.50



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